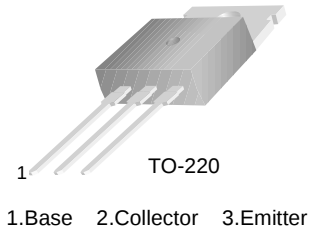


## BDW94/A/B/C

### Power Linear and Switching Applications

- Power Darlington TR
- Complement to BDW93, BDW93A, BDW93B and BDW93C respectively



### PNP Epitaxial Silicon Transistor

#### Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise noted

| Symbol    | Parameter                                        | Value      | Units            |
|-----------|--------------------------------------------------|------------|------------------|
| $V_{CBO}$ | Collector-Base Voltage                           |            |                  |
|           | : BDW94                                          | - 45       | V                |
|           | : BDW94A                                         | - 60       | V                |
|           | : BDW94B                                         | - 80       | V                |
|           | : BDW94C                                         | - 100      | V                |
| $V_{CEO}$ | Collector-Emitter Voltage                        |            |                  |
|           | : BDW94                                          | - 45       | V                |
|           | : BDW94A                                         | - 60       | V                |
|           | : BDW94B                                         | - 80       | V                |
|           | : BDW94C                                         | - 100      | V                |
| $I_C$     | Collector Current (DC)                           | - 12       | A                |
| $I_{CP}$  | *Collector Current (Pulse)                       | - 15       | A                |
| $I_B$     | Base Current                                     | - 0.2      | A                |
| $P_C$     | Collector Dissipation ( $T_C=25^\circ\text{C}$ ) | 80         | W                |
| $T_J$     | Junction Temperature                             | 150        | $^\circ\text{C}$ |
| $T_{STG}$ | Storage Temperature                              | - 65 ~ 150 | $^\circ\text{C}$ |

**Electrical Characteristics**  $T_C=25^{\circ}\text{C}$  unless otherwise noted

| Symbol         | Parameter                                                                           | Test Condition                                                                                                                            | Min.                          | Typ.           | Max.                             | Units                                                            |
|----------------|-------------------------------------------------------------------------------------|-------------------------------------------------------------------------------------------------------------------------------------------|-------------------------------|----------------|----------------------------------|------------------------------------------------------------------|
| $V_{CEO(sus)}$ | Collector-Emitter Sustaining Voltage<br>: BDW94<br>: BDW94A<br>: BDW94B<br>: BDW94C | $I_C = -100\text{mA}, I_E = 0$                                                                                                            | - 45<br>- 60<br>- 80<br>- 100 |                |                                  | V<br>V<br>V<br>V                                                 |
| $I_{CBO}$      | Collector Cut-off Current<br>: BDW94<br>: BDW94A<br>: BDW94B<br>: BDW94C            | $V_{CB} = -45\text{V}, I_E = 0$<br>$V_{CB} = -60\text{V}, I_E = 0$<br>$V_{CB} = -80\text{V}, I_E = 0$<br>$V_{CB} = -100\text{V}, I_E = 0$ |                               |                | - 100<br>- 100<br>- 100<br>- 100 | $\mu\text{A}$<br>$\mu\text{A}$<br>$\mu\text{A}$<br>$\mu\text{A}$ |
| $I_{CEO}$      | Collector Cut-off Current<br>: BDW94<br>: BDW94A<br>: BDW94B<br>: BDW94C            | $V_{CE} = -45\text{V}, I_B = 0$<br>$V_{CE} = -60\text{V}, I_B = 0$<br>$V_{CE} = -80\text{V}, I_B = 0$<br>$V_{CE} = -100\text{V}, I_B = 0$ |                               |                | - 1<br>- 1<br>- 1<br>- 1         | mA<br>mA<br>mA<br>mA                                             |
| $I_{EBO}$      | Emitter Cut-off Current                                                             | $V_{EB} = -5\text{V}, I_C = 0$                                                                                                            |                               |                | - 2                              | mA                                                               |
| $h_{FE}$       | * DC Current Gain                                                                   | $V_{CE} = -3\text{V}, I_C = -3\text{A}$<br>$V_{CE} = -3\text{V}, I_C = -5\text{A}$<br>$V_{CE} = -3\text{V}, I_C = -10\text{A}$            | 1000<br>750<br>100            |                | 20000                            |                                                                  |
| $V_{CE(sat)}$  | * Collector-Emitter Saturation Voltage                                              | $I_C = -5\text{A}, I_B = -20\text{mA}$<br>$I_C = -10\text{A}, I_B = -100\text{mA}$                                                        |                               |                | - 2<br>- 3                       | V<br>V                                                           |
| $V_{BE(sat)}$  | * Base-Emitter Saturation Voltage                                                   | $I_C = -5\text{A}, I_B = -20\text{mA}$<br>$I_C = -10\text{A}, I_B = -100\text{mA}$                                                        |                               |                | - 2.5<br>- 4                     | V<br>V                                                           |
| $V_F$          | * Parallel Diode Forward Voltage                                                    | $I_F = -5\text{A}$<br>$I_F = -10\text{A}$                                                                                                 |                               | - 1.3<br>- 1.8 | - 2<br>- 4                       | V<br>V                                                           |

\* Pulse Test: PW=300 $\mu\text{s}$ , duty Cycle =1.5% Pulsed

## Typical Characteristics

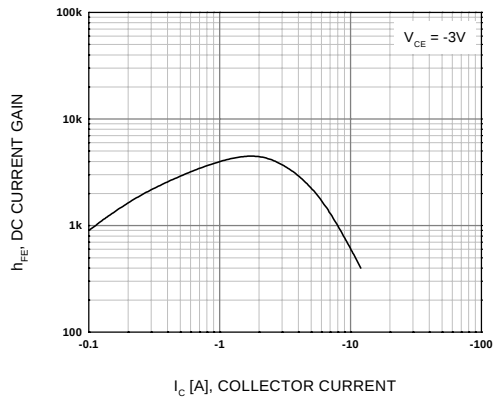


Figure 1. DC Current Gain

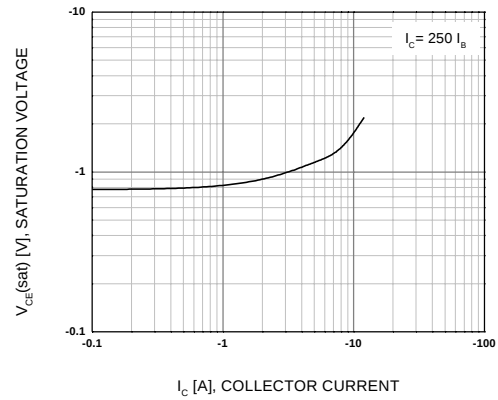


Figure 2. Collector-Emitter Saturation Voltage

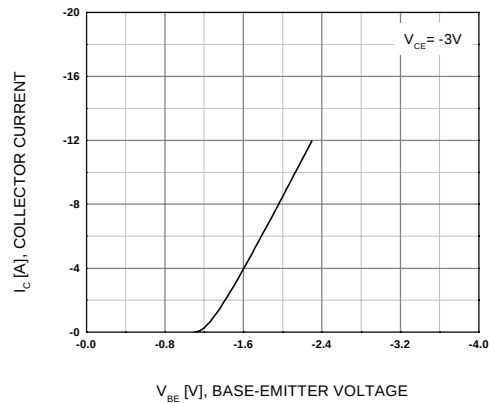


Figure 3. Base-Emitter On Voltage

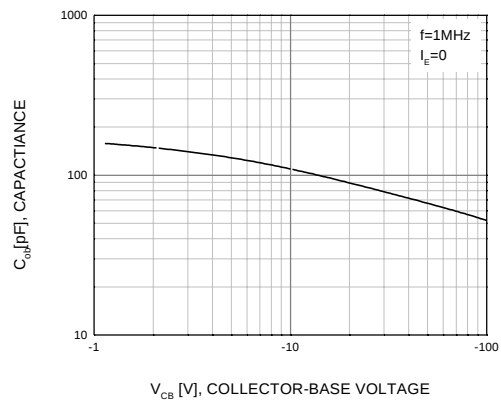


Figure 4. Output Capacitance

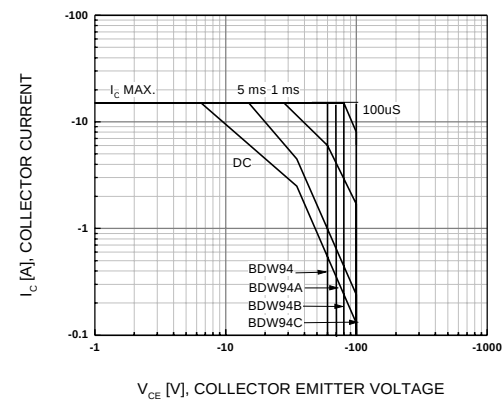


Figure 5. Safe Operating Area

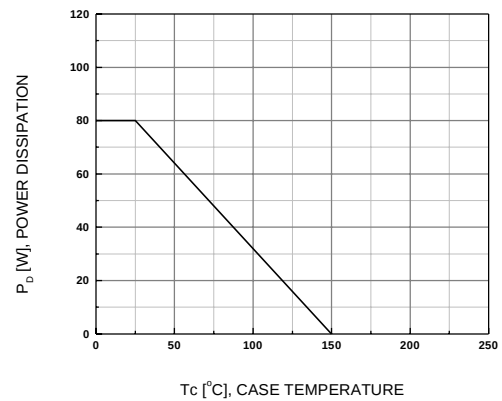


Figure 6. Power Derating

## BDW94/A/B/C

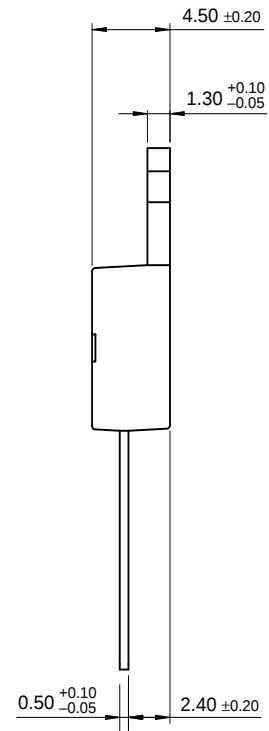
Technical drawing of a 3-pin connector showing front and top views with dimensions in millimeters.

**Front View Dimensions:**

- Overall width:  $9.90 \pm 0.20$
- Internal width:  $(8.70)$
- Top pin diameter:  $\varnothing 3.60 \pm 0.10$
- Top pin offset:  $1.30 \pm 0.10$
- Top pin height:  $(1.70)$
- Top pin to top edge distance:  $2.80 \pm 0.10$
- Top pin to bottom edge distance:  $15.90 \pm 0.20$
- Top pin to bottom edge distance (MAX.):  $18.95 \text{ MAX.}$
- Top pin to bottom edge distance (TYP.):  $(3.70)$
- Top pin to bottom edge distance (TYP.):  $(3.00)$
- Top pin to bottom edge distance (TYP.):  $(1.46)$
- Top pin to bottom edge distance (TYP.):  $(1.00)$
- Top pin to bottom edge distance (TYP.):  $1.27 \pm 0.10$
- Top pin to bottom edge distance (TYP.):  $1.52 \pm 0.10$
- Top pin to bottom edge distance (TYP.):  $0.80 \pm 0.10$
- Top pin to bottom edge distance (TYP.):  $2.54 \text{ TYP.}$
- Top pin to bottom edge distance (TYP.):  $[2.54 \pm 0.20]$
- Top pin to bottom edge distance (TYP.):  $2.54 \text{ TYP.}$
- Top pin to bottom edge distance (TYP.):  $[2.54 \pm 0.20]$
- Top pin to bottom edge distance (TYP.):  $13.08 \pm 0.20$
- Top pin to bottom edge distance (TYP.):  $10.08 \pm 0.30$
- Top pin to bottom edge distance (TYP.):  $45^\circ$

**Top View Dimensions:**

- Overall width:  $10.00 \pm 0.20$



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